

We Claim:

1. A semiconductor chip, comprising:

a top side with a surface;

said top side having a first portion to be covered by a potting compound or encapsulation compound of a housing;

said top side having a second portion to remain free of the potting compound or encapsulation compound;

a facilitator selected from the group consisting of a material applied thereon and an areal structure formed thereon for defining a variation in a degree of wettability or adhesion characteristics relative to the potting compound or the encapsulation compound for said surface in said first portion and said surface in said second portion, said facilitator rendering wetting, flowing, or adhesion of the potting compound or encapsulation compound in said second portion of said top side more difficult than in said first portion, and promoting an application of the potting compound or encapsulation compound exclusively on said first portion.

2. The semiconductor chip according to claim 1, wherein said first portion of said top side includes connection pads and/or bonding wires and said second portion of said top side includes at least one active component.

3. The semiconductor chip according to claim 2, wherein said second portion of said top side comprises a bearing area for a finger.

4. A method for producing a housing for a semiconductor chip, which comprises:

selecting a potting compound or encapsulation compound for forming a housing for the semiconductor chip;

processing a surface of the semiconductor chip in a second portion of a top side thereof with at least one process selected from the group consisting of coating with a material and areally structuring to form a configuration thereon rendering wetting, flowing, or adhesion of the potting compound or encapsulation compound more difficult than in a first portion of the top side, and promoting application of the potting compound or encapsulation compound exclusively on the first portion of the top side; and

subsequently applying the potting compound or encapsulation compound to the top side of the semiconductor chip and thereby:

covering the first portion of the top side with the potting compound or encapsulation compound; and

leaving the second portion of the top side free of the potting compound or encapsulation compound.

5. The method according to claim 4, which comprises, prior to application of the potting compound or encapsulation compound, covering the second portion of the top side of the semiconductor chip with a material entering into a chemical reaction with the potting compound or encapsulation compound or initiates and/or promotes a chemical reaction between a further applied material and the potting compound or encapsulation compound, in such a way that this chemical reaction stops flowing of the potting compound or encapsulation compound on this portion of the top side or makes it more difficult for the potting compound or encapsulation compound to adhere on this portion of the top side.